

RBA160N04AHPF-4UA01

40V – 160A – N-channel Power MOS FET

Application : Automotive

R07DS1344EJ0200

Rev.2.00

Jul. 8, 2020

Description

The RBA160N04AHPF-4UA01 is N-channel MOS Field Effect Transistor designed for high current switching applications.

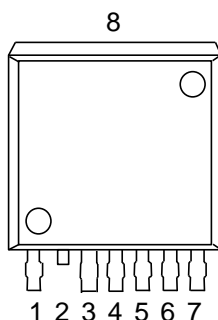
Features

- Super low on-state resistance
 $R_{DS(on)} = 1.25 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 80 \text{ A)}$
- Low input capacitance
 $C_{iss} = 8800 \text{ pF TYP. (} V_{DS} = 25 \text{ V)}$
- Designed for automotive application and AEC-Q101 qualified
- Pb-free (This product does not contain Pb in the external electrode)

Ordering Information

Part No.	Quantity	Shipping container
RBA160N04AHPF-4UA01#GB0	800pcs/reel	Taping

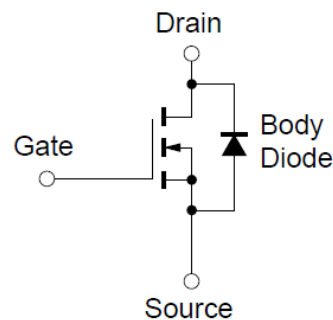
Outline



1. Gate
2. Drain
- 3, 4, 5, 6, 7. Source
8. Drain (Fin)

TO-263-7pin-SHL* (MP-25ZU)

* Short Head & Lead



Equivalent circuit

Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Absolute Maximum Ratings

(T_A=25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	40	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25 °C)	I _{D(DC)}	±160	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±640	A
Total Power Dissipation (T _C = 25 °C)	P _{T1}	250	W
Total Power Dissipation (T _A = 25 °C)	P _{T2}	1.8	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to 175	°C
Repetitive Avalanche Current ^{Note2}	I _{AR}	55	A
Repetitive Avalanche Energy ^{Note3}	E _{AR}	303	mJ

Note 1. P_W ≤ 10 μs, Duty Cycle ≤ 1%2. V_{GS} = 20 → 0V, R_G = 25 Ω3. L = 100μH, V_{DD} = 20V, V_{GS} = 20 → 0V, R_G = 25 Ω

Thermal Resistance

Channel to Case Thermal Resistance	R _{th(ch-C)}	0.60	°C/W
Channel to Ambient Thermal Resistance	R _{th(ch-A)}	83.3	°C/W

Electrical Characteristics

(T_A=25°C)

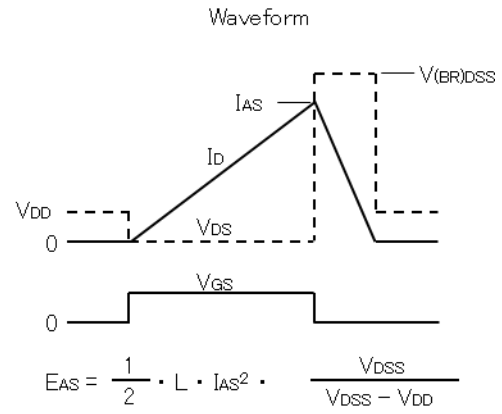
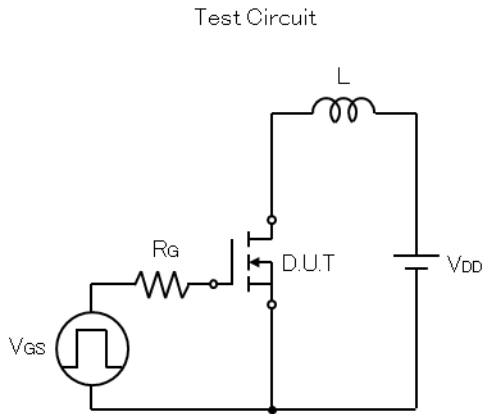
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 40 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±100	nA	V _{GS} = ± 20 V, V _{DS} = 0 V
Gate to Source Threshold Voltage	V _{GS(th)}	2.0	3.0	4.0	V	V _{DS} = V _{GS} , I _D = 250 μA
Drain to Source On-state Resistance	R _{DS(on)} ^{Note4}		1.05	1.25	mΩ	V _{GS} = 10 V, I _D = 80 A
Input Capacitance	C _{iss} ^{Note5}		8800	13200	pF	V _{DS} = 25 V V _{GS} = 0 V f = 1 MHz
Output Capacitance	C _{oss} ^{Note5}		980	1470	pF	
Reverse Transfer Capacitance	C _{rss} ^{Note5}		530	960	pF	
Turn-on Delay Time	t _{d(on)} ^{Note5}		32	64	ns	V _{DD} = 20 V, I _D = 80 A V _{GS} = 10 V
Rise Time	t _r ^{Note5}		22	53	ns	
Turn-off Delay Time	t _{d(off)} ^{Note5}		97	194	ns	R _G = 0 Ω
Fall Time	t _f ^{Note5}		22	53	ns	
Total Gate Charge	Q _G ^{Note5}		157	236	nC	V _{DD} = 32 V V _{GS} = 10 V I _D = 160 A
Gate to Source Charge	Q _{GS} ^{Note5}		37		nC	
Gate to Drain Charge	Q _{GD} ^{Note5}		40		nC	
Body Diode Forward Voltage	V _{F(S-D)} ^{Note4}		0.9	1.5	V	I _F = 160 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr} ^{Note5}		71		ns	I _F = 160 A, V _{GS} = 0 V
Reverse Recovery Charge	Q _{rr} ^{Note5}		92		nC	di/dt = 100 A/μs

Note 4. Pulse test

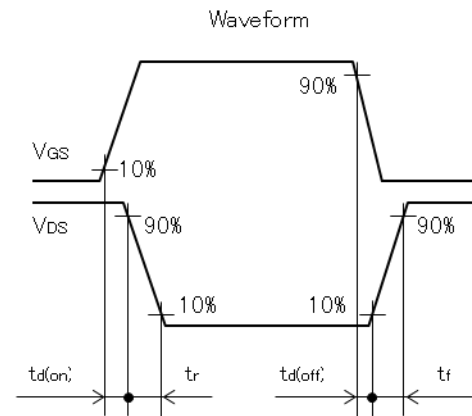
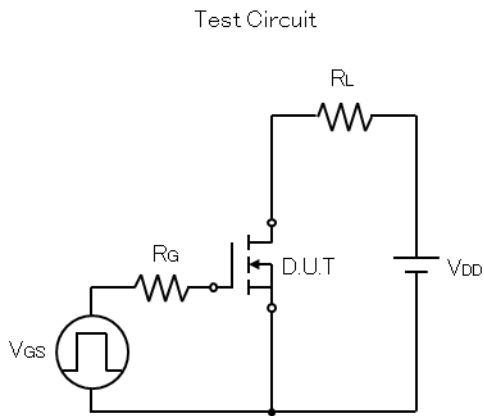
Note 5. Refer value

Test Circuit

Avalanche

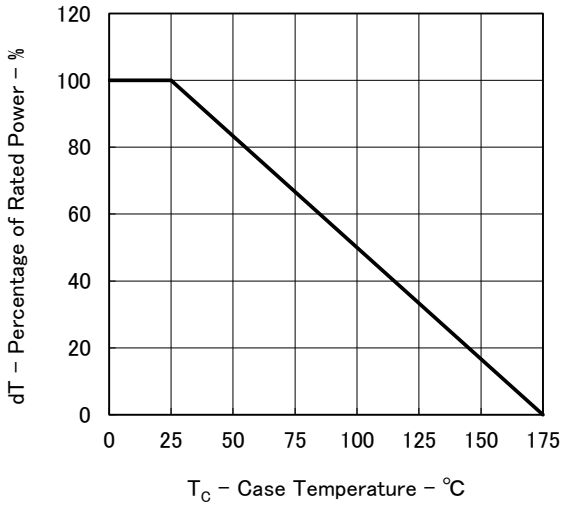


Switching Time

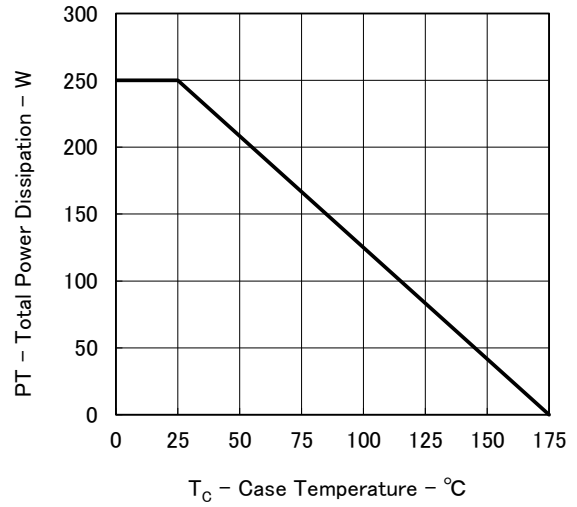


Typical Characteristics (TA = 25°C)

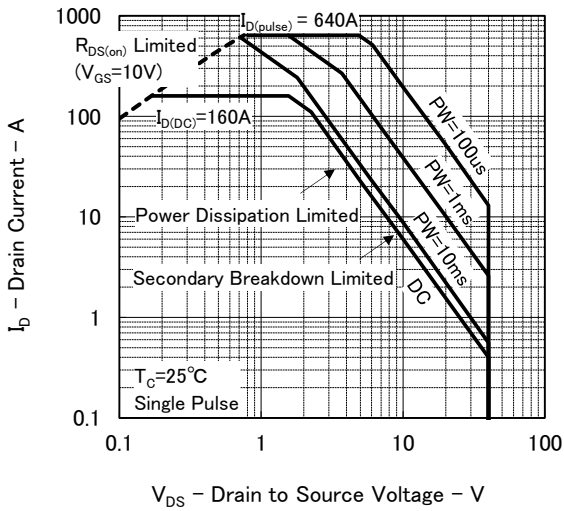
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



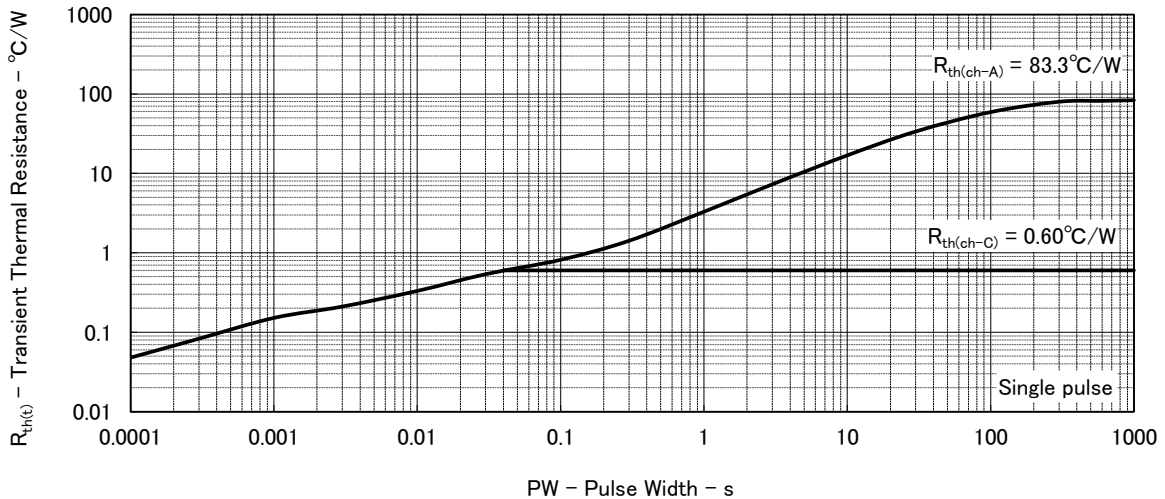
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



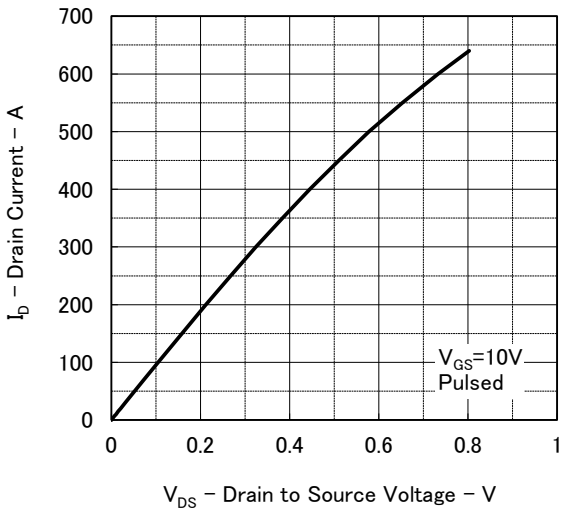
FORWARD BIAS SAFE OPERATING AREA



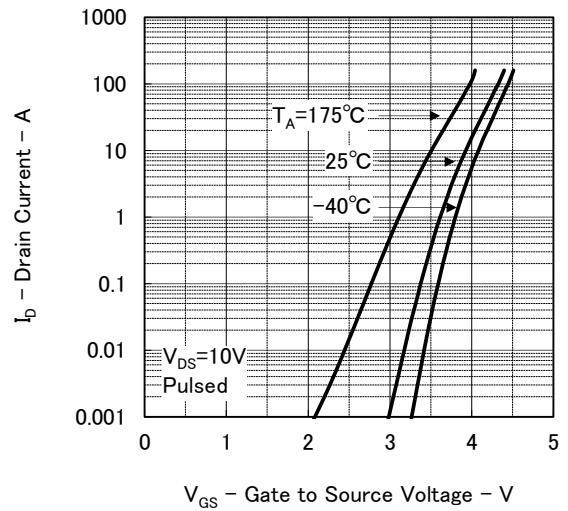
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



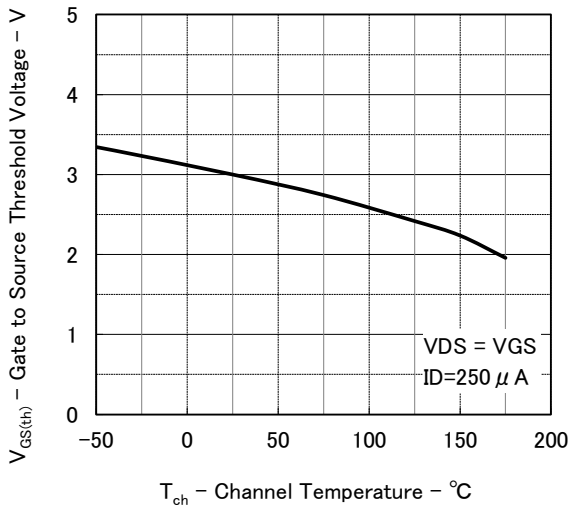
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



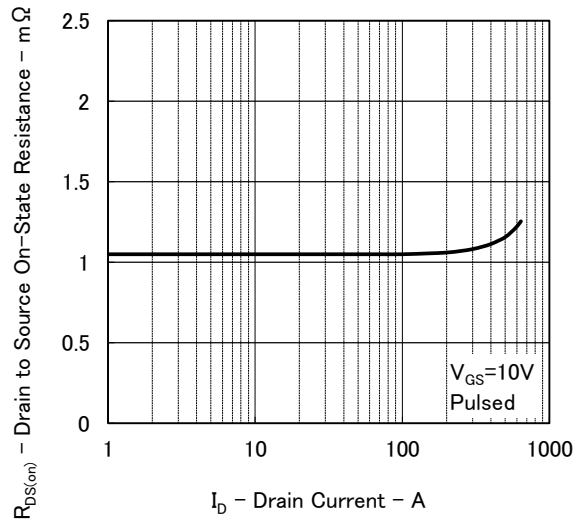
FORWARD TRANSFER CHARACTERISTICS



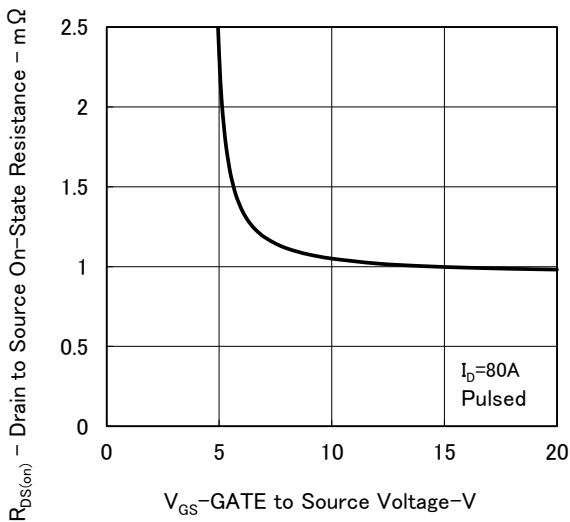
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



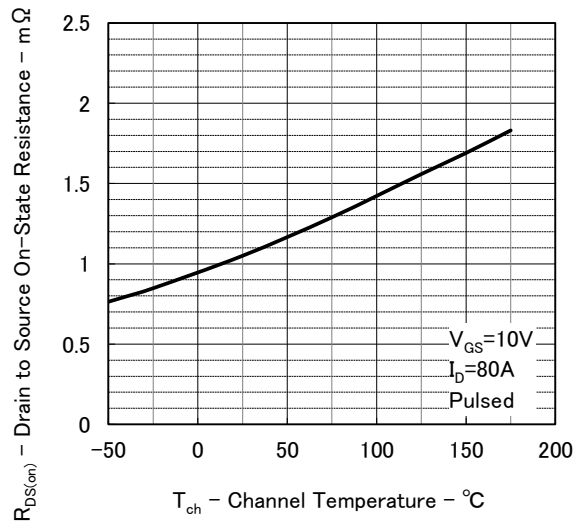
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



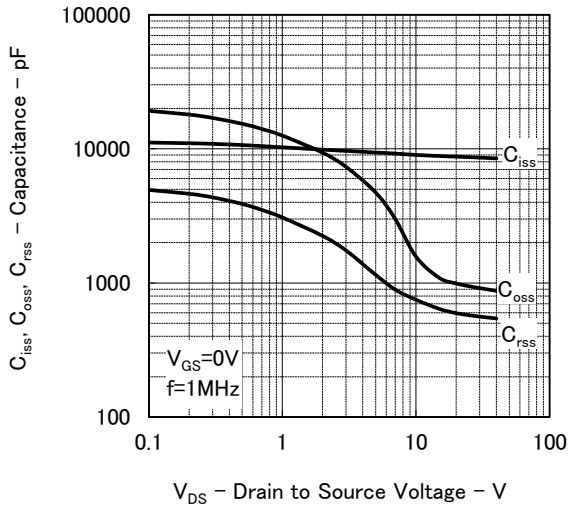
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



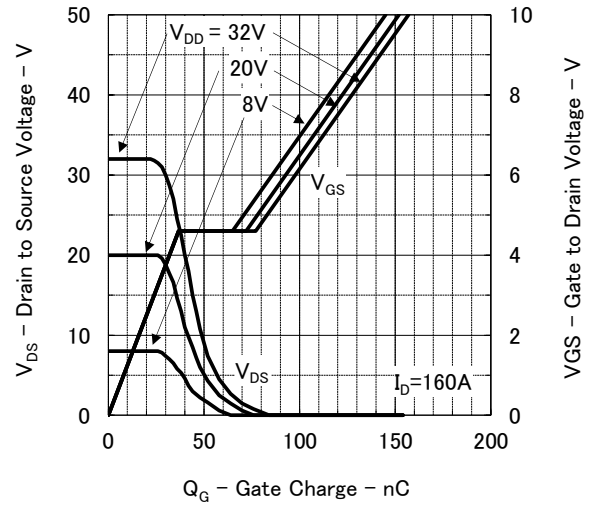
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



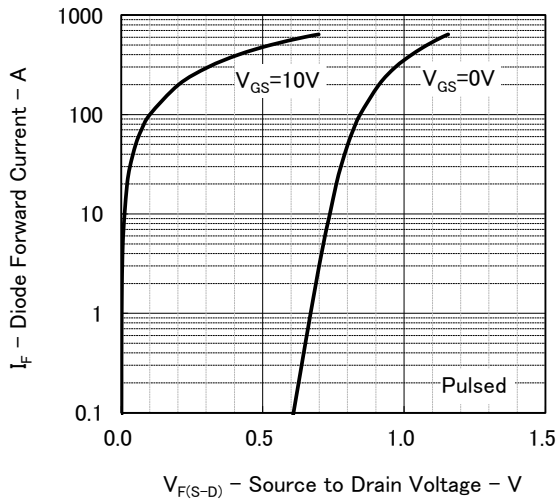
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



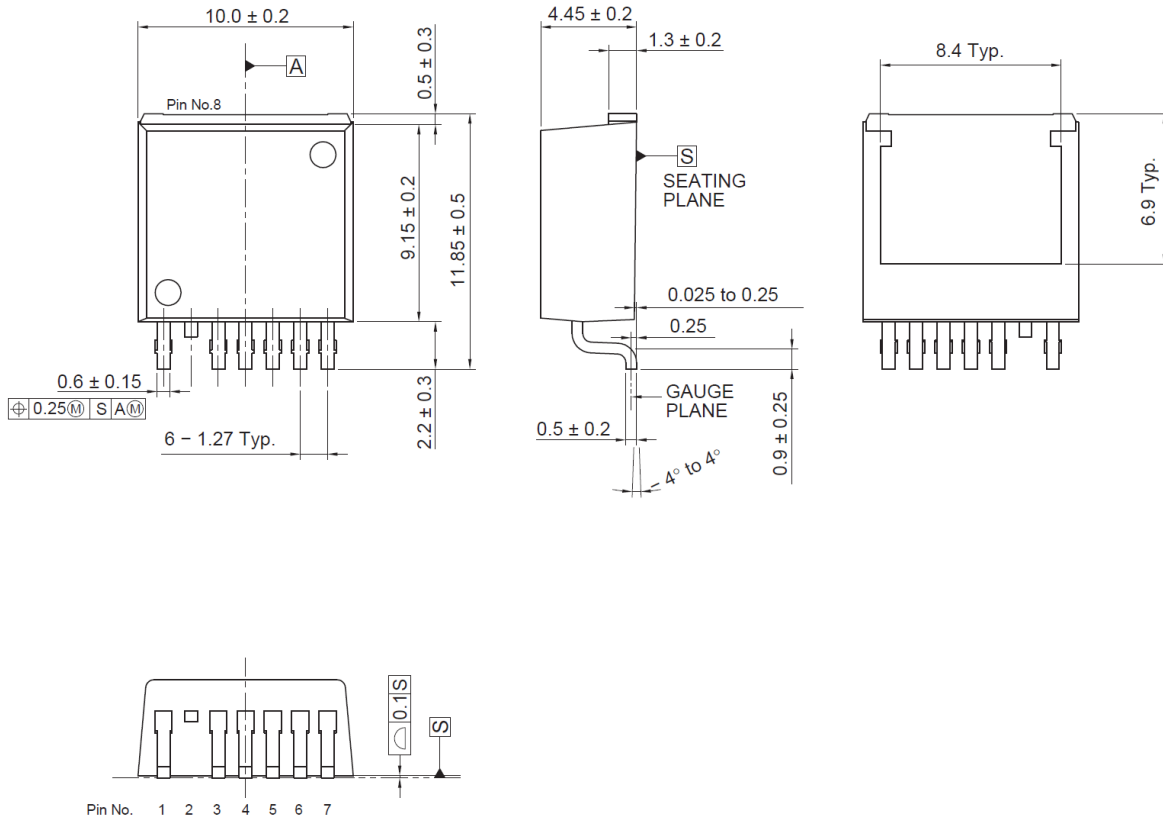
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



Package Dimensions

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]	Package Name
—	PRSS0008DC-A	—	1.39	MP-25ZU

Unit: mm



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Renesas Electronics Corporation
TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan

Renesas Electronics America Inc.
1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.
Tel: +1-408-432-8888, Fax: +1-408-434-5351

Renesas Electronics Canada Limited
9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 101-T01, Floor 1, Building 7, Yard No. 7, 8th Street, Shangdi, Haidian District, Beijing 100085, China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai 200333, China
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit No 3A-1 Level 3A Tower 8 UOA Business Park, No 1 Jalan Pengaturcara U1/51A, Seksyen U1, 40150 Shah Alam, Selangor, Malaysia
Tel: +60-3-5022-1288, Fax: +60-3-5022-1290

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India
Tel: +91-80-67208700

Renesas Electronics Korea Co., Ltd.
17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5338